

## 30V N-Channel Enhancement Mode MOSFET

### Description

The AP3400EI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

$V_{DS} = 30V$   $I_D = 3.0A$

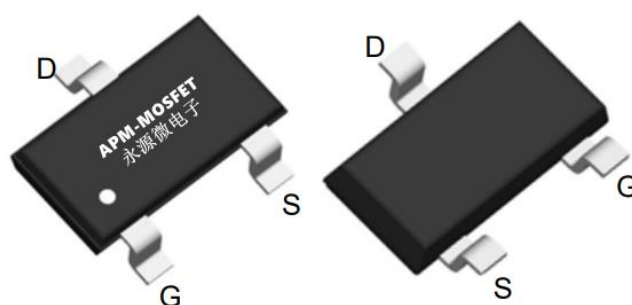
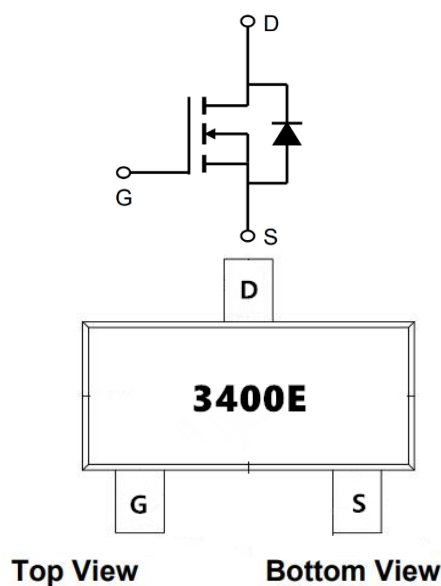
$R_{DS(ON)} < 98m\Omega$  @  $V_{GS} = 4.5V$  (Type: 80m $\Omega$ )

### Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP3400EI	SOT23L	3400E	3000

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	3.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	1.8	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	9.6	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	80	$^\circ C/W$

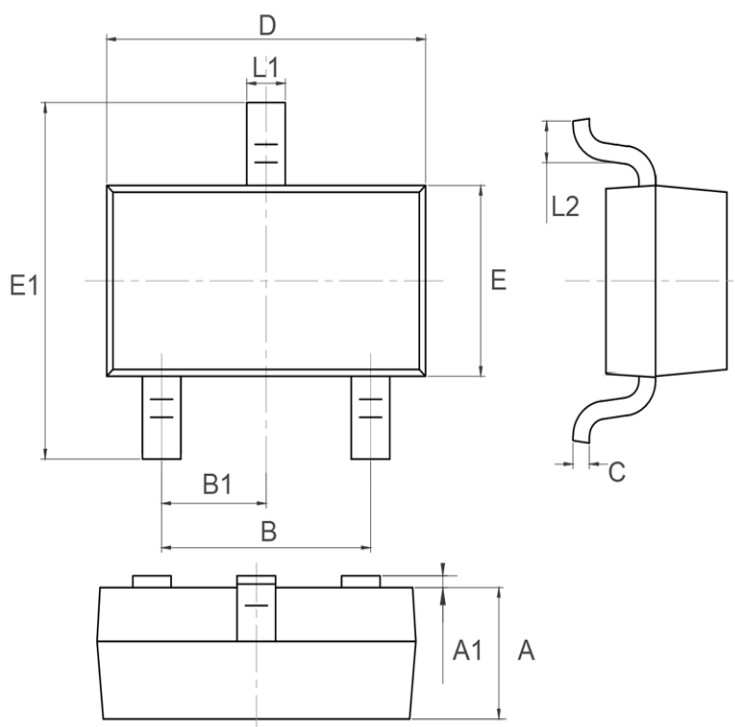
**30V N-Channel Enhancement Mode MOSFET**
**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	30	34	---	V
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=4.5V$ , $I_D=3A$	---	80	98	m $\Omega$
		$V_{GS}=2.5V$ , $I_D=2A$	---	95	110	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	0.5	0.85	1.2	V
IDSS	Drain-Source Leakage Current	$V_{DS}=30V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$	---	---	1	$\mu A$
		$V_{DS}=30V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 12V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V$ , $I_D=3A$	---	10.5	---	S
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V$ , $V_{GS}=4.5V$ , $I_D=3A$	---	4.6	---	nC
$Q_{gs}$	Gate-Source Charge		---	0.7	---	
$Q_{gd}$	Gate-Drain Charge		---	1.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V$ , $V_{GS}=4.5V$ , $R_G=3.3\Omega$ , $I_D=3A$	---	1.6	---	ns
$T_r$	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14	---	
$T_f$	Fall Time		---	7	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	310	---	pF
$C_{oss}$	Output Capacitance		---	49	---	
$C_{rss}$	Reverse Transfer Capacitance		---	35	---	
IS	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	3.6	A
VSD	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=1A$ , $T_J=25^{\circ}\text{C}$	---	---	1.2	V

**Note :**

- 1、The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3、The power dissipation is limited by 150 $^{\circ}\text{C}$  junction temperature
- 4、The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

## Package Mechanical Data-SOT23L-Single



Symbol	Dim in mm		
	Min	Typ	Max
A	0.9	1	1.1
A1	0	0.05	0.1
B	1.8	1.9	2
B1	0.95TYP		
C	0.08	0.115	0.15
D	2.8	2.9	3
E	1.2	1.3	1.4
E1	2.25	2.4	2.55
L1	0.3	0.4	0.5
L2	0.2	0.35	0.5

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Edition	Date	Change
REV1.0	2020/9/11	Initial release

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